



General Description

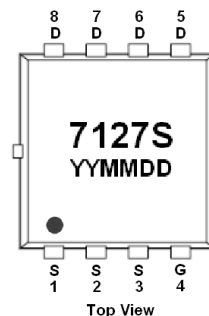
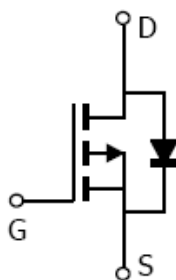
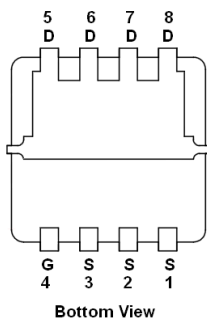
AFP7127S, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- $I_D = -10A, R_{DS(ON)} = 15m\Omega @ V_{GS} = -10V$
- $I_D = -7A, R_{DS(ON)} = 20m\Omega @ V_{GS} = -4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- DFN3.3X3.3-8L package design

Pin Description (DFN3.3X3.3-8L)



Application

- DC-DC Converter
- POL

Pin Define

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP7127SFN308RG	7127S	DFN3.3X3.3-8L	Tape & Reel	5000 EA

※ YY year code

※ MM month code

※ DD date code

※ AFP7127SFN308RG : 13" Tape & Reel ; Pb- Free ; Halogen -Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	-30	V
Gate –Source Voltage	V _{GSS}	±20	V
Continuous Drain Current(T _J =150°C)	I _D	T _A =25°C	-10
		T _A =70°C	-8
Pulsed Drain Current	I _{DM}	-50	A
Continuous Source Current(Diode Conduction)	I _S	-16	A
Power Dissipation	P _D	T _A =25°C	3.8
		T _A =70°C	2
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	120	°C/W

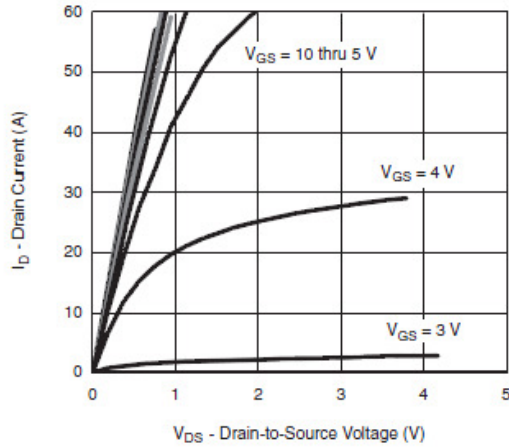
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

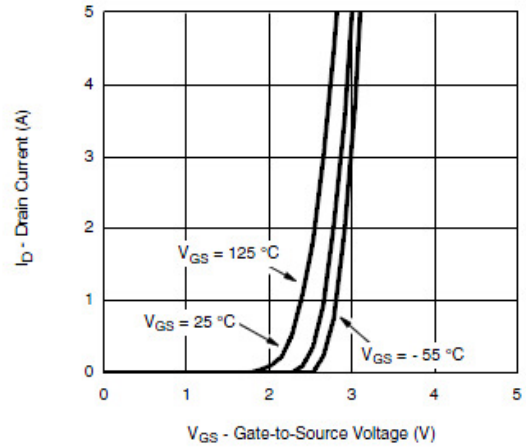
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250uA	-30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1.0		-2.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±25V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V			-1	uA
		V _{DS} =-24V, V _{GS} =0V T _J =85°C			-30	
On-State Drain Current	I _{D(on)}	V _{DS} ≤ -10V, V _{GS} =-10V	-30			A
		V _{DS} ≤ -5V, V _{GS} =-4.5V	-5			
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-10.0A		10	15	mΩ
		V _{GS} =-4.5V, I _D =-7.0A		15	20	
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-10A		23		S
Diode Forward Voltage	V _{SD}	I _S =-2.3A, V _{GS} =0V		-0.7	-1.3	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =-15V, V _{GS} =-4.5V I _D =-10.0A		20	35	nC
Gate-Source Charge	Q _{gs}			6		
Gate-Drain Charge	Q _{gd}			10		
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V f=1MHz		1960		pF
Output Capacitance	C _{oss}			380		
Reverse Transfer Capacitance	C _{rss}			325		
Turn-On Time	t _{d(on)}	V _{DD} =-15V, R _L =3Ω I _D =-10.0A, V _{GEN} =-10V R _G =1Ω		10	25	ns
	t _r			15	30	
Turn-Off Time	t _{d(off)}			30	60	
	t _f			10	20	



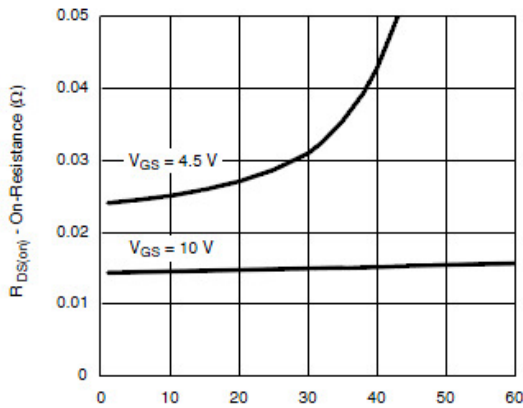
Typical Characteristics



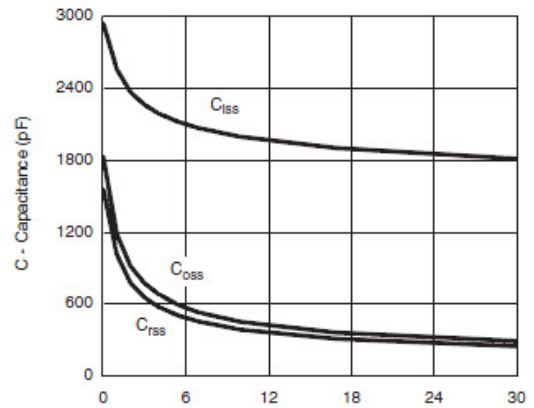
Output Characteristics



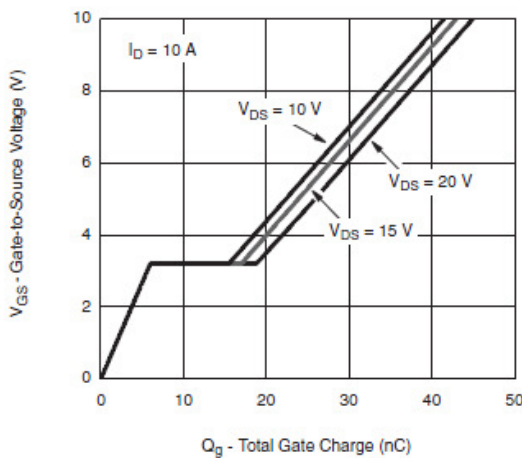
Transfer Characteristics



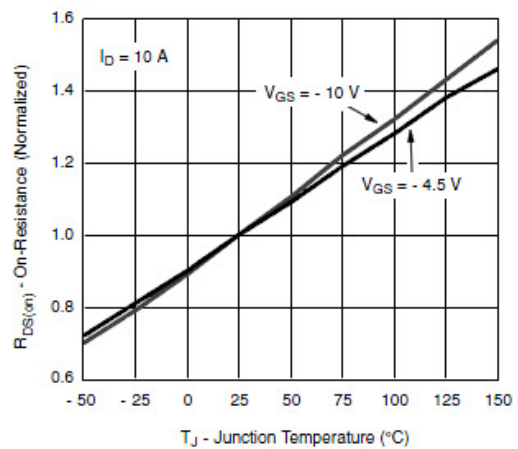
On-Resistance vs. Drain Current



Capacitance



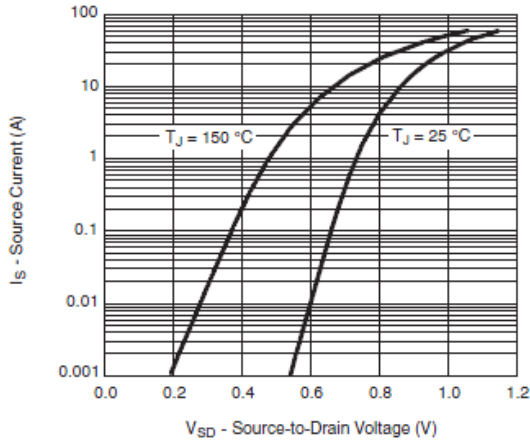
Gate Charge



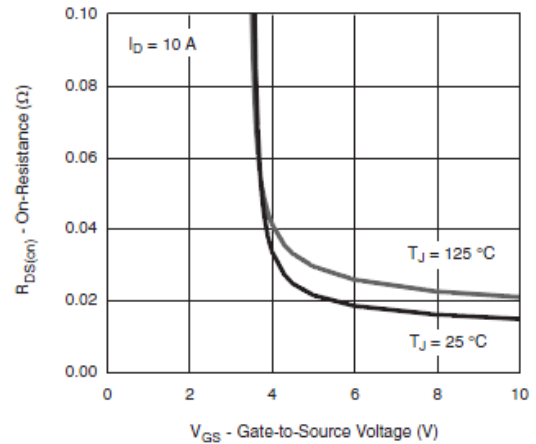
On-Resistance vs. Junction Temperature



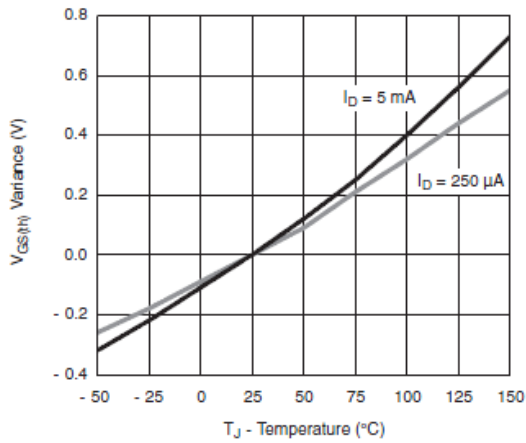
Typical Characteristics



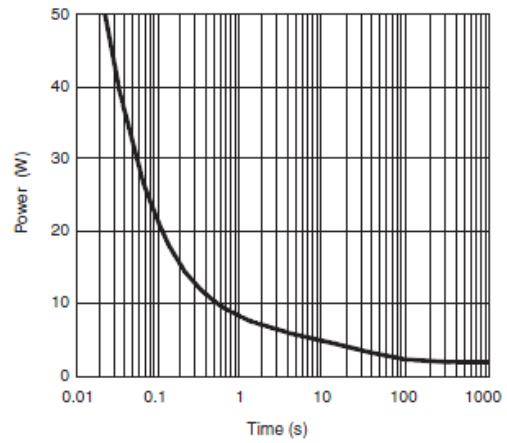
Source-Drain Diode Forward Voltage



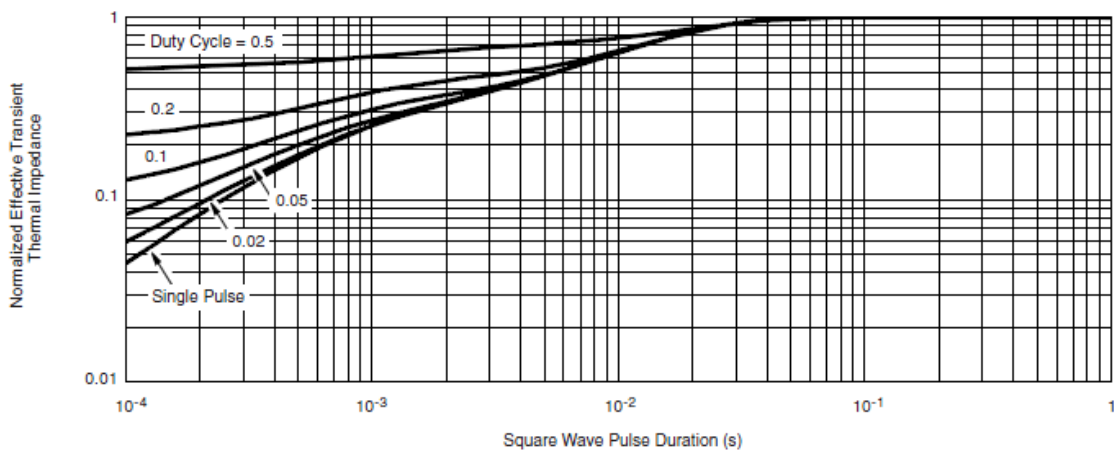
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

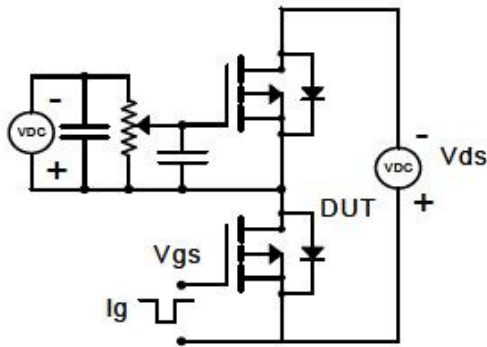


Normalized Thermal Transient Impedance, Junction-to-Case

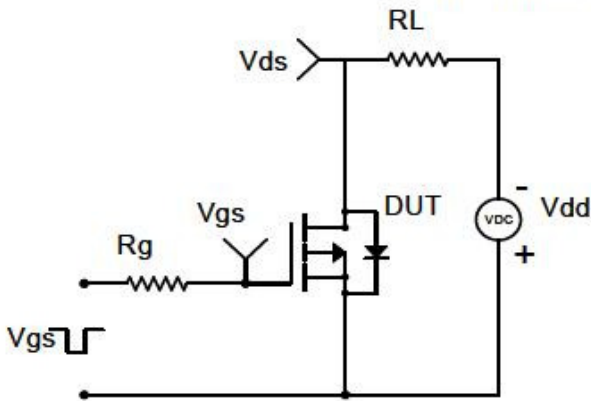


Typical Characteristics

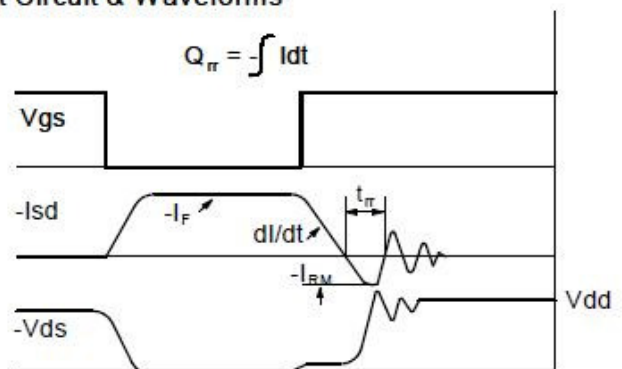
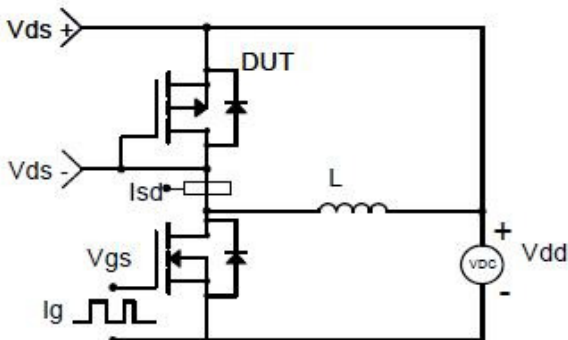
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

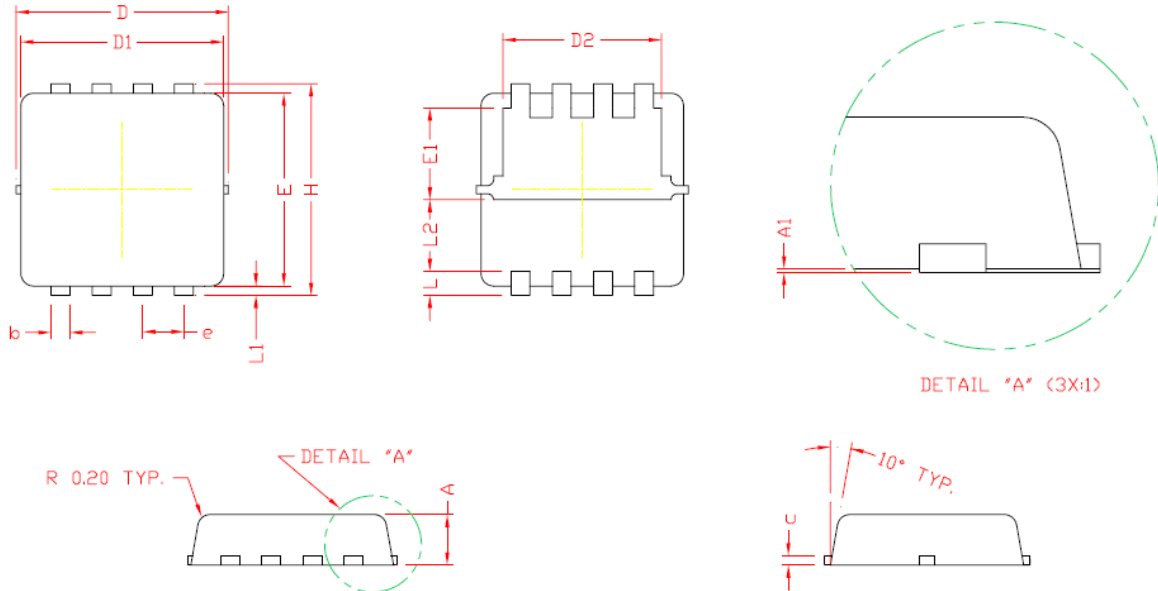


Diode Recovery Test Circuit & Waveforms





Package Information (DFN3.3X3.3-8L)



DIMENSIONS

REF.	Millimeters		REF.	Millimeters	
	Min.	Max.		Min.	Max.
A	0.70	0.90	E	3.00	3.20
A1	0.00	0.05	E1	1.35	1.55
b	0.24	0.35	e	0.65 BSC.	
c	0.10	0.20	H	3.20	3.40
D	3.25	3.40	L	0.30	0.50
D1	3.05	3.25	L1	0.10	0.20
D2	2.40	2.60	L2	1.13 Ref.	

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